L Number	Hits	Search Text	DB	Time stamp
1	11	"semiconductor memory device" and ("first region" near2 "first	USPAT;	2004/02/22 16:57
		direction")	US-PGPUB; EPO; JPO;	
			DERWENT	
2	10	("semiconductor memory device" and ("first region" near2 "first	USPAT;	2004/02/22 16:42
	10	direction")) and "second region"	US-PGPUB;	2004/02/22 10:12
		3	EPO; JPO;	
			DERWENT	
5	20	"word line" and ("first region" near2 "first direction")	USPAT;	2004/02/22 16:46
			US-PGPUB;	
			EPO; JPO;	
7	10	("word line" and ("first region" near? "first direction")) and	DERWENT	2004/02/22 46:47
7	19	("word line" and ("first region" near2 "first direction")) and select\$8	USPAT; US-PGPUB;	2004/02/22 16:47
		Selecipo	EPO; JPO;	
			DERWENT	
8	12	(("word line" and ("first region" near2 "first direction")) and	USPAT;	2004/02/22 16:47
•		select\$8) and activat\$8	US-PGPUB;	200 1102/22 10:11
			EPO; JPO;	
			DERWENT	
9	9	((("word line" and ("first region" near2 "first direction")) and	USPAT;	2004/02/22 16:57
		select\$8) and activat\$8) and "sense amplifier"	US-PGPUB;	
			EPO; JPO;	
	0.40		DERWENT	0004/00/0040 50
10	346	"semiconductor memory device" and "open bit line"	USPAT;	2004/02/22 16:58
			US-PGPUB;	
			EPO; JPO; DERWENT	
11	16	("semiconductor memory device" and "open bit line") and "first	USPAT;	2004/02/22 16:58
''	10	region"	US-PGPUB;	200-702/22 10.50
			EPO; JPO;	
			DERWENT	
12	61	("semiconductor memory device" and "open bit line") and "first	USPAT;	2004/02/22 16:58
.		direction"	US-PGPUB;	
			EPO; JPO;	
			DERWENT	
13	55	("semiconductor memory device" and "open bit line") and	USPAT;	2004/02/22 16:58
1		"second direction"	US-PGPUB;	
ļ			EPO; JPO; DERWENT	
14	16	("semiconductor memory device" and "open bit line") and	USPAT:	2004/02/22 16:58
.,	.0	"second region"	US-PGPUB;	200 1/02/22 10:00
			EPO; JPO;	
			DERWENT	
15	8	(("semiconductor memory device" and "open bit line") and	USPAT;	2004/02/22 16:59
		"second region") and perpendicular	US-PGPUB;	
			EPO; JPO;	
16	•	(//nominanduster mamon, device) and llance his line)) and	DERWENT	2004/02/22 40:50
16	2	(("semiconductor memory device" and "open bit line") and "first region") and (("semiconductor memory device" and	USPAT; US-PGPUB;	2004/02/22 16:59
		"open bit line") and "first direction") and (("semiconductor	EPO; JPO;	
		memory device" and "open bit line") and "second direction")	DERWENT	
		and (("semiconductor memory device" and "open bit line") and	DERWEIT	
		"second region") and ((("semiconductor memory device" and		
		"open bit line") and "second region") and perpendicular)		
-	1	"20040017716"	USPAT;	2004/02/20 02:05
			US-PGPUB;	
			EPO; JPO;	
		//ICC20020II\ /ICC4C007II\ /ICC2C27C7II\	DERWENT	2004/00/20 04:50
-	4	(("6639822") or ("6545897") or ("6373776") or	USPAT;	2004/02/20 01:56
_	5	("6370054")).PN. (("6639822") or ("6545897") or ("6373776") or	US-PGPUB USPAT;	2004/02/20 02:02
-	5		US-PGPUB;	2007102120 02.02
ļ		1 (D.57(10:24 1) PN		1
		("6370054")).PN.	EPO; JPO;	

-	2	"20030112695"	USPAT;	2004/02/20 01:58
			US-PGPUB;	
]		EPO; JPO;	
		"20040000540"	DERWENT	2004/02/20 02:00
-	2	"20010009519"	USPAT; US-PGPUB;	2004/02/20 02:00
	}		EPO; JPO;	
			DERWENT	
<u> </u>	2	"20020080640"	USPAT;	2004/02/20 02:01
	_	2502000010	US-PGPUB;	200 1/02/20 02:01
	İ		EPO; JPO;	
	İ		DERWENT	
-	5	"20040017716" or "20030112695" or "20010009519" or	USPAT;	2004/02/20 02:01
		"20020080640"	US-PGPUB;	
			EPO; JPO;	
			DERWENT	
-	9	("20040017716" or "20030112695" or "20010009519" or	USPAT;	2004/02/20 02:02
		"20020080640") or ((("6639822") or ("6545897") or	US-PGPUB;	
		("6373776") or ("6370054")).PN.)	EPO; JPO;	
			DERWENT	
-	37122	"semiconductor memory device"	USPAT;	2004/02/20 02:06
			US-PGPUB;	
		·	EPO; JPO; DERWENT	
	17	semiconductor memory device" and ("first region" near4 "first"	USPAT;	2004/02/22 16:41
-	17	direction")	US-PGPUB;	2004/02/22 10.41
		direction)	EPO; JPO;	
			DERWENT	
_	47	"semiconductor memory device" and first adj2 region adj6 first	USPAT;	2004/02/20 02:09
		adj2 direction	US-PGPUB;	200 1702720 02.00
			EPO; JPO;	
			DERWENT	
-	41	("semiconductor memory device" and first adj2 region adj6 first	USPAT;	2004/02/20 02:10
		adj2 direction) and second adj2 direction	US-PGPUB;	
			EPO; JPO;	
	0.10		DERWENT	
-	210	"semiconductor memory device" and "second direction	USPAT;	2004/02/20 02:11
		perpendicular" near3 "first direction"	US-PGPUB;	
			EPO; JPO; DERWENT	
-	209	"semiconductor memory device" and "second direction	USPAT;	2004/02/20 02:13
	203	perpendicular" adj3 "first direction"	US-PGPUB:	200 1102120 02.10
		Fare and more an agreement	EPO; JPO;	
			DERWENT	
-	1	"semiconductor memory device" and "selected first region"	USPAT;	2004/02/20 02:14
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
-	42	"semiconductor memory device" and select\$6 adj2 first adj2	USPAT;	2004/02/20 02:14
		region	US-PGPUB;	
			EPO; JPO;	
	19	("semiconductor memory device" and select\$6 adj2 first adj2	DERWENT USPAT;	2004/02/20 02:15
1	'9	region) and select\$6 adj2 second adj2 region	US-PGPUB;	2004/02/20 02.15
		10g.0.1/ and 00100ty0 dajz 000011d dajz 16g1011	EPO; JPO;	
			DERWENT	
_	19	("semiconductor memory device" and select\$6 adj2 first adj2	USPAT;	2004/02/20 02:15
		region) and select\$6 adj2 second adj2 region	US-PGPUB	
-	13	("semiconductor memory device" and select\$6 adj2 first adj2	USPAT	2004/02/20 02:15
		region) and select\$6 adj2 second adj2 region		
-	6	("semiconductor memory device" and select\$6 adj2 first adj2	US-PGPUB	2004/02/20 03:02
	L	region) and select\$6 adj2 second adj2 region		